



PATENT

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS: WILFRIED VON AMMON ET AL. -11
SERIAL NO.: 10/809,070 GROUP: 2812
FILED: MARCH 25, 2004
TITLE: METHOD AND DEVICE FOR THE PRODUCTION OF A SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL, AND SILICON SEMICONDUCTOR WAFERS WITH DETERMINED DEFECT DISTRIBUTIONS

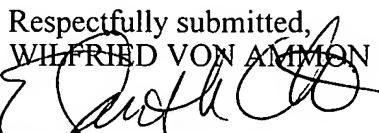
SUBMISSION OF INFORMATION DISCLOSURE
STATEMENT OF DR. WOLFGANG STAUDACHER

MAIL STOP AMENDMENT
Hon. Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Applicants wish to bring to the attention of the Patent Examiner the attached Information Disclosure Statement, duly signed by Dr. Wolfgang Staudacher, and the references listed on the enclosed Form PTO-1449 and attached thereto. These references were cited in the Specification. Since the instant Information Disclosure Statement is being filed before a first Office Action on the merits, it is believed that no fee is due. It is respectfully requested that the foregoing Information Disclosure Statement be incorporated into the official file of the present patent application.

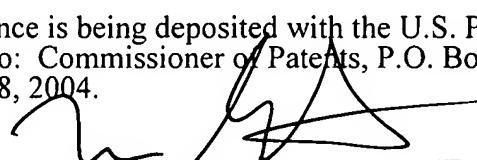
Respectfully submitted,
WILFRIED VON AMMON ET AL. -11


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Elizabeth Collard Richter, Reg. No. 35,103
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ECR:ea

Encs: Information Disclosure Statement of Dr. Wolfgang Staudacher; PTO-1449 form and eight (8) references.

I hereby certify that this correspondence is being deposited with the U.S. Postal Service as first class mail in an envelope addressed to: Commissioner of Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450, on June 18, 2004.


Maria Guastella



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

VON AMMON ET AL. - 11

Serial Number: 10/809,070

Group Art Unit: 2812

Filed: MARCH 25, 2004

For: METHOD AND DEVICE FOR THE PRODUCTION OF A SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL, AND SILICON SEMICONDUCTOR WAFERS WITH DETERMINED DEFECT DISTRIBUTIONS

Information Disclosure Statement

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

Sir or Madam:

I, Wolfgang Staudacher, associated with the preparation and prosecution of the above-identified application, residing at Seebauerstraße 4, 81735 München, Germany, wish to call the attention of the Patent Examiner to the references enumerated on the enclosed PTO Form-1449.

I believe the documents enumerated on the enclosed Form PTO-1449 and attached thereto, are cited in the enclosed application and may be material to the examination of the application.

Therefore, it is respectfully requested that the foregoing Information Disclosure Statement be considered by the Examiner and incorporated into the file of this application.

I wish to comment as follows concerning the prior art references enumerated on PTO Form-1449:

Zulehner/Huber in Crystals 8, Springer Verlag, Berlin Heidelberg, 1982, pp. 44-46, cited in the application, is already in English language.

US 2002/0092461 A1, cited in the application, is already in English language.

“Numerical investigation of silicon melt flow in large diameter CZ-crystal growth and the influence of steady and dynamic magnetic fields”, Journal of Crystal Growth, 230 (2001), pp. 92-99, cited in the application, is already in English language.

Ammon, Journal of Crystal Growth, 151, 1995, pp. 273-277, cited in the application, is already in English language.

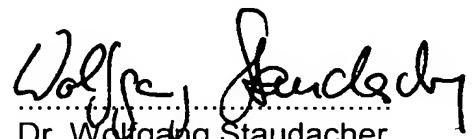
Eidenzon/Puzanov in Inorganic Materials, Vol. 33, No. 3, 1997, pp. 219-255, cited in the application, is already in English language.

US 6,153,008, cited in the application, is already in English language.

US 5,567,399, cited in the application, is already in English language.

H. Bender, J. Vanhellemont, R. Schmolke, „High Resolution Structure Imaging of Octahedral Void Defects in As-Grown Czochralski Silicon”, Japan. J. Appl. Phys. 36 (1997), L 1217 - L1220, Part 2, No. 9 A/B, cited in the application, is already in English language.

Signed this 4th day of May, 2003.



Dr. Wolfgang Staudacher

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. : <u>ST10242</u>	SERIAL NO. <u>10/809,070</u>
JUN 21 2004 LIST OF REFERENCES CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: <u>von Ammon et al. - 11</u>	
		FILING DATE: <u>MARCH 25, 2004</u>	GROUP: <u>2812</u>

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	2002/0092461	7/18/02	Virbulis et al.			
	AB	6,153,008	11/28/00	von Ammon et al.			
	AC	5,567,399	10/22/96	von Ammon et al.			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AL							
	AM							
	AN							
	AO							
	AP							

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

	AR	Zulehner/tuber in Crystals 8, Springer Verlag, Berlin Heidelberg, 1982, pp. 44-46
		Journal of Crystal Growth, 230 (2001), pp. 92-99
	AS	Ammon, Journal of Crystal Growth, 151, 1995, pp. 273-277
EXAMINER		DATE CONSIDERED

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. : <u>ST 10242</u>	SERIAL NO. <u>10/809,070</u>
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	AR	<u>Eidenzon/Puzanov in Inorganic Materials, Vol. 33, No. 3, 1997, pp. 219-255</u>					
	AS	<u>H. Bender, J. Vanhellemont, R. Schmolke, Japan. J. Appl. Phys. 36 (1997), L1217-L1220, Part 2, No. 9 A/13</u>					
	AT						

EXAMINER	DATE CONSIDERED
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